

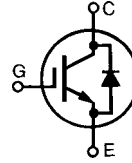
IGBT with Diode

IXSR 35N120BD1

ISOPLUS 247™

(Electrically Isolated Backside)

Short Circuit SOA Capability

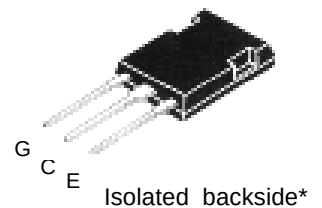


$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 70 \text{ A} \\ V_{CE(sat)} &= 3.6 \text{ V} \\ t_{fi(typ)} &= 180 \text{ ns} \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	70	A
I_{C90}	$T_C = 90^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	140	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 90$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15 \text{ V}$, $V_{CE} = 720 \text{ V}$, $T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT	250 W
		Diode	150 W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ leads-to housing	2500	V~
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Weight		5	g

ISOPLUS247™

E 153432



G = Gate, C = Collector,
E = Emitter

* Patent pending

Features

- DCB Isolated mounting tab
- Meets TO-247AD package outline
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Advantages

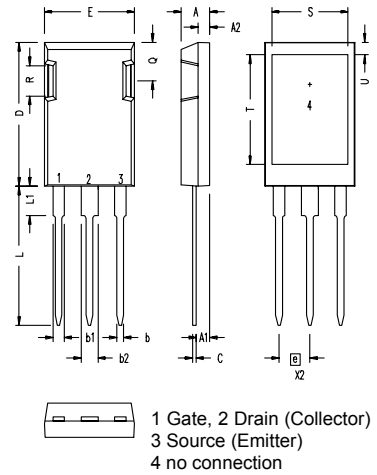
- Easy assembly
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 3 \text{ mA}$, $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	3		6 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$	$T_J = 25^\circ\text{C}$		1 mA
	$V_{GE} = 0 \text{ V}$	$T_J = 150^\circ\text{C}$		3 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_T$, $V_{GE} = 15 \text{ V}$			3.6 V

① Device must be heatsunk for high temperature measurements to avoid thermal runaway.
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_T$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	16	23	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		3600	pF
C_{oss}			315	pF
C_{rss}			75	pF
Q_g	$I_C = I_T$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5\text{ V}_{CES}$		120	nC
Q_{ge}			33	nC
Q_{gc}			49	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_T$, $V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8\text{ V}_{CES}$, $R_G = 2.7\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		36	ns
t_{ri}			27	ns
$t_{d(off)}$			160	300 ns
t_{fi}			180	300 ns
E_{off}			5	9 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_T$, $V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8\text{ V}_{CES}$, $R_G = 2.7\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		38	ns
t_{ri}			29	ns
E_{on}			6	mJ
$t_{d(off)}$			240	ns
t_{fi}			340	ns
E_{off}			9	mJ
R_{thJC}				0.5 K/W
R_{thCK}		0.15		K/W

ISOPLUS 247 OUTLINE



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

Reverse Diode (FRED)		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
V_F	$I_F = I_T$, $V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			2.75 V 1.85
I_{RM}	$I_F = I_T$, $V_{GE} = 0\text{ V}$, $-di_F/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ $I_F = 1\text{ A}$; $-di_F/dt = 200\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$		7	14.3 A
t_{rr}			40	ns
R_{thJC}				0.83 K/W

Note: 1. $I_T = 35\text{ A}$